

RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

### DESCRIPTION

The BL817S-C Series of devices each consist of an Infrared Emitting Diodes, optically coupled to a phototransistor detector. They are packaged in a 4-pin DIP package and available in Wide-lead spacing and SMD option.

DIP4L



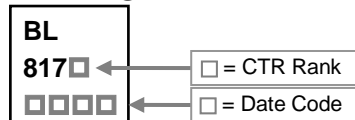
### FEATURES

- Current Transfer Ratio (CTR: 50%~600% @ $I_F=5mA$ ,  $V_{CE}=5V$ )
- High Isolation Voltage Between Input and Output ( $V_{iso}=5000V$  rms)
- Creepage Distance > 7.62mm
- UL/CUL Approved

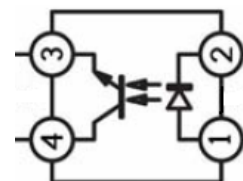
### APPLICATIONS

- Programmable Controllers
- System Appliances, Measuring Instruments
- Telecommunication Equipments
- Home Appliances, Such as Fan Heaters, etc.
- Signal Transmission Between Circuits of Different Potentials and Impedances

### MARKING



Top View



### ORDER INFORMATION

Part Number	Type
BL817S-□-C	Lead (Pb)-free and Halogen-free

\*□=Rank

### RANK TABLE OF CURRENT TRANSFER RATIO CTR

Product-Rank	BL817S-L-C	BL817S-A-C	BL817S-B-C	BL817S-C-C	BL817S-D-C	BL817S-E-C
Range(%)	50~100	80~160	130~260	200~400	300~600	50~600

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Input	Forward Current	$I_F$	50	mA
	Peak Forward Current <sup>1</sup>	$I_{FM}$	1	A
	Reverse Voltage	$V_R$	6	V
	Power Dissipation	$P_D$	70	mW
Output	Collector-Emitter Voltage	$V_{CEO}$	80	V
	Emitter-Collector Voltage	$V_{ECO}$	7	V
	Collector Current	$I_C$	50	mA
	Collector Power Dissipation	$P_C$	150	mW

**ABSOLUTE MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Total Power Dissipation	$P_{tot}$	200	mW
Isolation Voltage <sup>2</sup>	$V_{iso}$	5000	V <sub>rms</sub>
Rated Impulse Isolation Voltage	$V_{IOTM}$	6000	V
Rated Repetitive Peak Isolation Voltage	$V_{IORM}$	630	V
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	430	°C/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	350	
Thermal Resistance Junction- Lead	$R_{\theta JL}$	368	
Operating Temperature	$T_{opr}$	-55~110	°C
Storage Temperature	$T_{stg}$	-55~125	
Soldering Temperature <sup>3</sup>	$T_{sol}$	260	

Notes:

1. Pulse width  $\leq 1\mu\text{s}$ , Duty ratio: 0.001.
2. 40~60% RH, AC for 1 minute.
3. For 10 Seconds.

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Input	Forward Voltage	$V_F$	-	1.2	1.4	V	$I_F=20\text{mA}$
	Peak Forward Voltage	$V_{FM}$	-	-	3	V	$I_{FM}=0.5\text{A}$
	Reverse Current	$I_R$	-	-	10	$\mu\text{A}$	$V_R=4\text{V}$
	Input Capacitance	$C_i$	-	30	-	pF	$V=0, f=1\text{KHz}$
Output	Collector-Emitter Dark Current	$I_{CEO}$	-	-	100	nA	$V_{CE}=20\text{V}, I_F=0$
	Collector-Emitter Breakdown Voltage	$BV_{CEO}$	80	-	-	V	$I_C=0.1\text{mA}, I_F=0$
	Emitter-Collector Breakdown Voltage	$BV_{ECO}$	7	-	-	V	$I_E=10\mu\text{A}, I_F=0$
Transfer Characteristics	Collector Current	$I_C$	2.5	-	30	mA	$V_{CE}=5\text{V}, I_F=5\text{mA}$
	Current Transfer Ratio	CTR	50	-	600	%	
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	0.1	0.2	V	$I_F=20\text{mA}, I_C=1\text{mA}$
	Isolation Resistance	$R_{iso}$	$1 \times 10^{12}$	-	-	$\Omega$	$V_{IO}=500\text{V}_{DC}$ 40~60%R.H.
	Floating Capacitance	$C_f$	-	0.6	-	pF	$V=0, f=1\text{MHz}$
	Cut-off Frequency	$f_c$	-	80	-	KHz	$V_{CE}=5\text{V}, I_C=2\text{mA},$ $R_L=100\Omega, -3\text{dB}$
	Turn On Time	$T_{on}$	-	4	-	$\mu\text{s}$	$V_{CE}=2\text{V}, I_C=2\text{mA},$ $R_L=100\Omega$
Turn Off Time	$T_{off}$	-	3	-			

**CHARACTERISTIC CURVE**

Fig. 1 Allowable Forward Current vs. Ambient Temperature

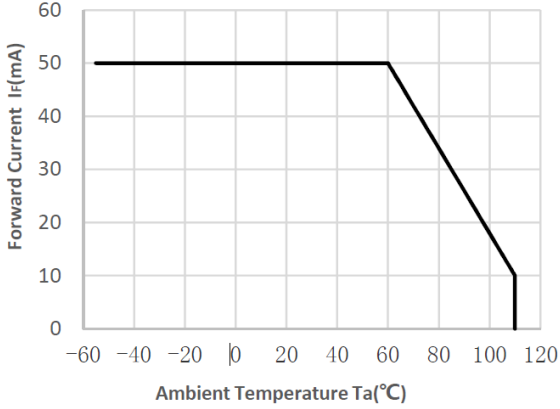


Fig. 2 Allowable collector power dissipation vs. Ambient Temperature(°C)

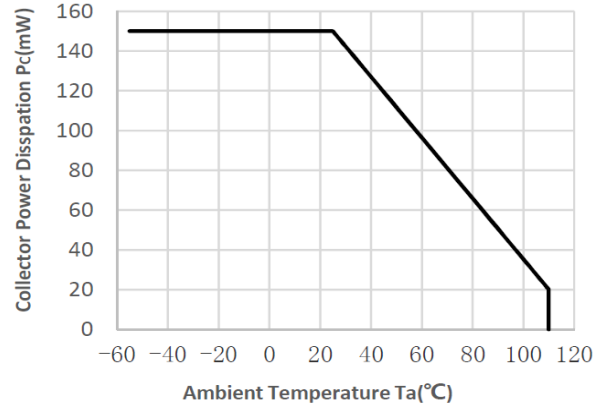


Fig. 3 Relative Current Transfer Ratio vs. Forward Current

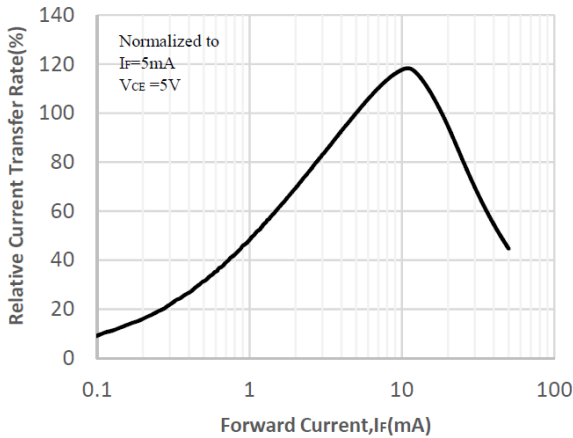


Fig. 4 Forward Current vs. Forward Voltage

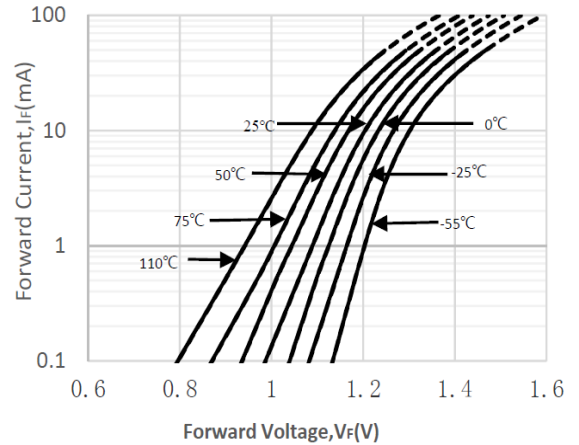


Fig. 5 Collector Current vs. Collector-emitter Voltage

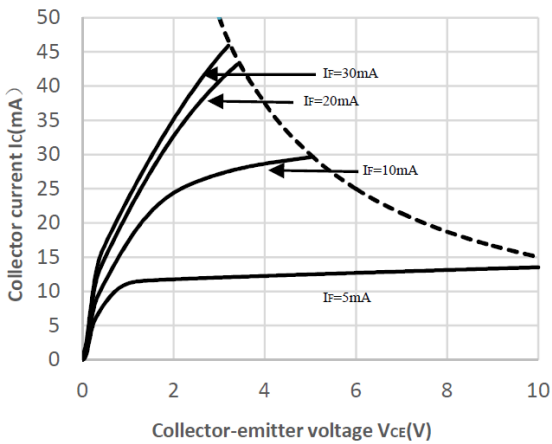
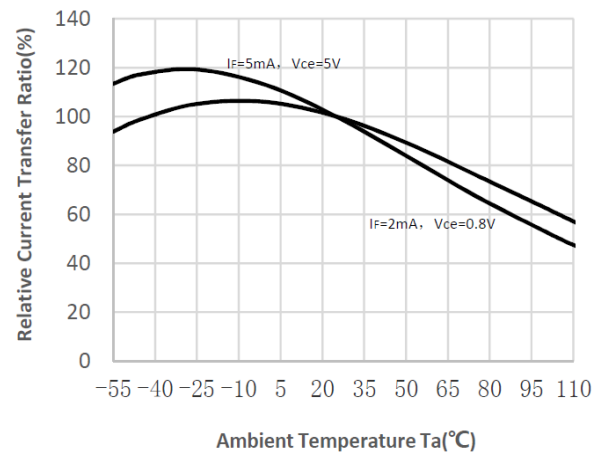


Fig. 6 Relative Current Transfer Ratio vs. Ambient Temperature



**CHARACTERISTIC CURVE**

Fig. 7 Collector-emitter Saturation Voltage vs. Ambient Temperature

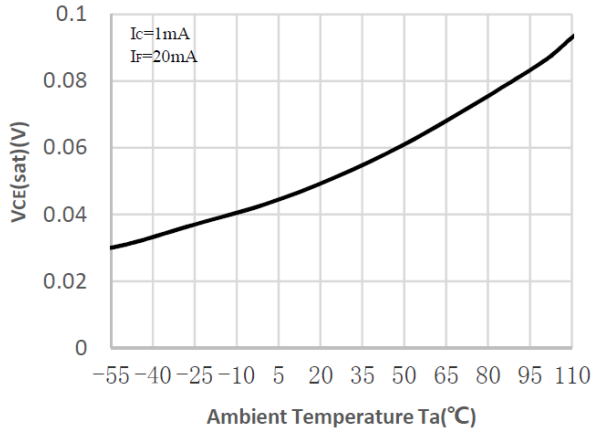


Fig. 8 Collector Dark Current vs. Ambient Temperature

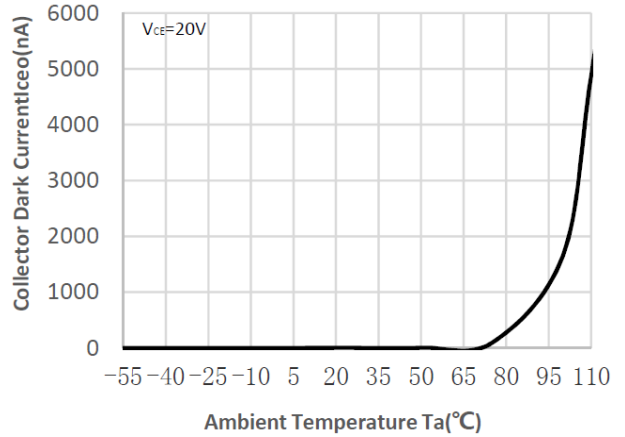


Fig. 9 Response Time vs. Load Resistance

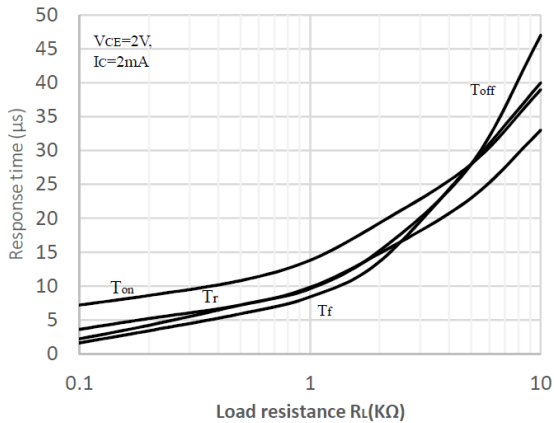


Fig. 10 Frequency Response

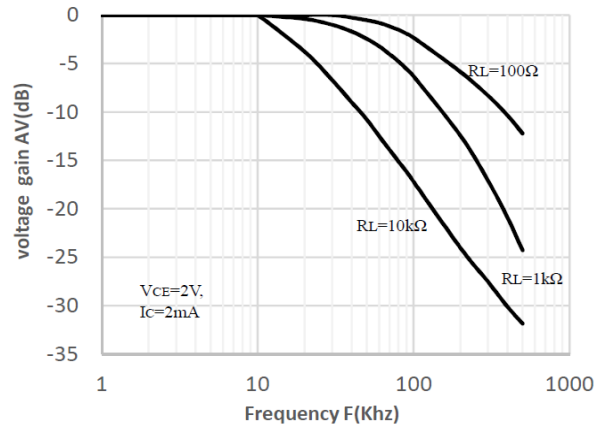


Fig. 11 Collector-emitter Saturation Voltage vs. Forward Current

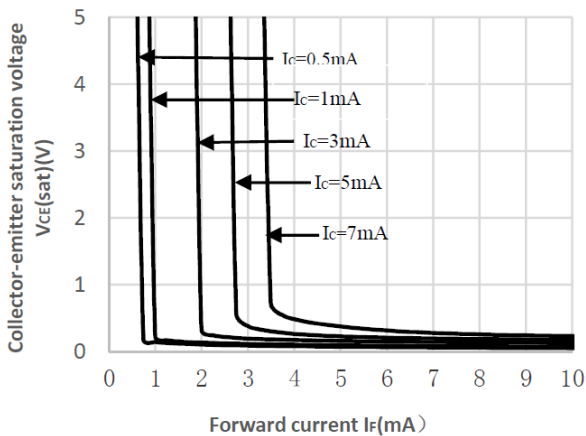
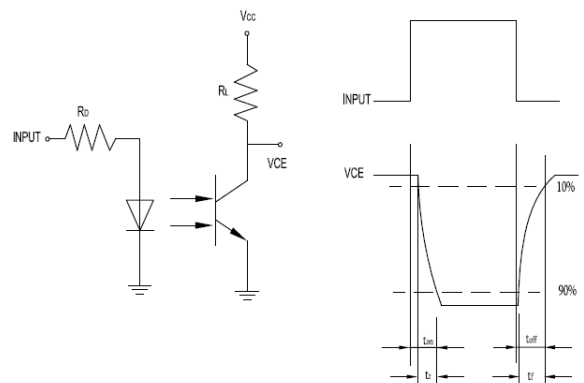
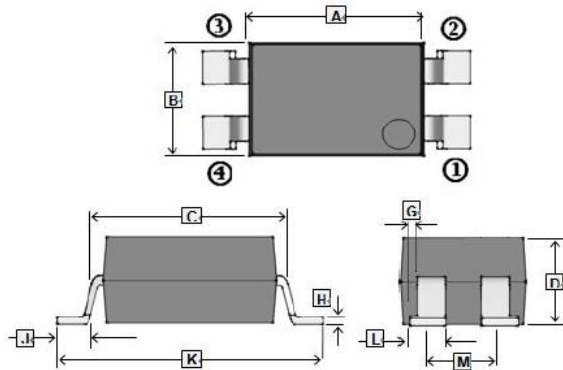


Fig. 12 Switching Time Test Circuit & Waveforms



**PACKAGE OUTLINE DIMENSIONS**

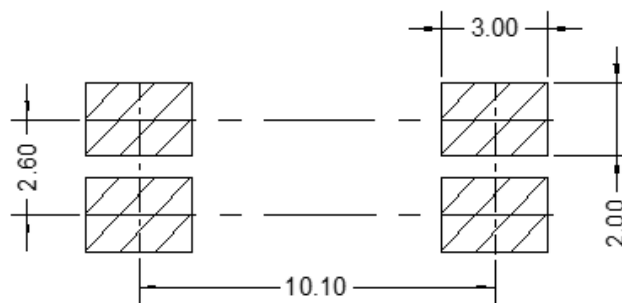
**DIP4L**



REF.	Millimeter	
	Min.	Max.
A	6.40	6.60
B	4.50	4.70
C	7.90	8.30
D	3.28	3.68
G	0.30	0.50
H	-	0.20
J	0.90	1.20
K	9.80	10.30
L	1.15	1.35
M	2.49	2.69

**MOUNTING PAD LAYOUT**

**DIP4L**



\*Dimensions in millimeters